

**RECEIVED  
CENTRAL FAX CENTER**

**NOV 20 2006**

**In the Claims:**

1.-20. (Cancelled)

21. (Previously Presented) A method of forming electrically connected contacting parts of a component integrated into a semiconductor substrate, the method comprising:

providing a first contact hole in an insulating layer; and

filling the contact hole with contact material so that the contact material is electrically connected to a line;

wherein a hard mask that is used to pattern the contact hole is subsequently re-patterned to define a conductor line trench which is connected thereto.

22. (Previously Presented) The method of claim 21 wherein said hard mask is made from polycrystalline silicon.

23. (Previously Presented) The method of claim 21 further comprising patterning said hard mask by means of a dry etching process.

24. (Previously Presented) The method of claim 23 wherein said dry etching process comprises using at least one of the group SF<sub>6</sub>, HBr and He/O<sub>2</sub>.

25. (Previously Presented) The method of claim 21 further comprising depositing a liner on a surface of said contact hole and line prior to said step of filling.

26. (Previously Presented) The method of claim 25 wherein said liner is selected from the group consisting of Ti and TiN.

27. (Previously Presented) The method of claim 21 wherein said step of filling the contact hole with contact material comprising filling said contact hole with tungsten.
28. (Previously Presented) A method of forming a contact hole and a conductor trench connecting to said contact hole in an insulating layer using a common hard mask, the method comprising:
- providing said insulating layer;
  - providing said hard mask patterned to form said contact hole;
  - etching said contact hole in said insulating layer;
  - re-patterning said hard mask to form said conductor trench connected to said contact hole;
  - etching said conductor trench in said insulating layer; and
  - filling said contact hole and said conductor trench with a conductive material such that said conductive material in said conductor trench and said contact hole are electrically connected.
29. (Previously Presented) The method of claim 28 wherein said hard mask is made from polycrystalline silicon.
30. (Currently Amended) ~~The method of claim 28 further comprising covering said insulating layer with an ARC layer to fill said contact hole prior to said step of re-patterning said hard mask.~~ A method of forming a contact hole and a conductor trench connecting to said contact hole in an insulating layer using a common hard mask, the method comprising:

providing said insulating layer;  
providing said hard mask patterned to form said contact hole;  
etching said contact hole in said insulating layer;  
covering said insulating layer with an ARC layer to fill said contact hole;  
re-patterning said hard mask subsequent to said step of covering the insulating  
layer with an ARC layer to form said conductor trench connected to said contact hole;  
etching said conductor trench in said insulating layer; and  
filling said contact hole and said conductor trench with a conductive material such  
that said conductive material in said conductor trench and said contact hole are  
electrically connected.

31. (Previously Presented) The method of claim 28 wherein said step of repatterning said hard mask comprises etching said hard mask by means of a dry etching process.

32. (Previously Presented) The method of claim 31 wherein said dry etching process comprises using at least one of the group  $\text{SF}_6$ ,  $\text{HBr}$  and  $\text{He/O}_2$ .

33. (Previously Presented) The method of claim 28 further comprising the step of depositing a liner on a surface of said contact hole and conductor trench prior to said step of filling.

34. (Previously Presented) The method of claim 28 wherein said step of filling said contact hole with conductive material comprises filling said contact hole with tungsten.

35. (Previously Presented) The method of claim 33 wherein said liner is selected from the group consisting of Ti and TiN.